

# Voltage vs. Current Driven CCRF Discharges: Differences in Electron and Ion Dynamics

S. Wilczek<sup>1</sup>, J. Trieschmann<sup>1</sup>, J. Schulze<sup>1</sup>, R. P. Brinkmann<sup>1</sup>, A. Derzsi<sup>2</sup>, P. Hartmann<sup>2</sup>, Z. Donkó<sup>2</sup>, T. Mussenbrock<sup>1</sup>

<sup>1</sup>Ruhr-University Bochum, Germany
<sup>2</sup>Wigner Research Centre for Physics, Budapest, Hungary

# Power input for asymmetric ccrf discharges



- most ccrf discharges are asymmetric, electrode surfaces are naturally grounded
- experiments: power is coupled via matchbox into the system
- simulation and models: voltage and current sources are frequently used
- what are the differences in low pressure ccrf discharges?

RUE

# **Resonance phenomena in asymmetric ccrf discharges**



- global model to determine plasma series resonance (PSR)
- self-excitation of PSR is eliminated using current sources (no harmonics)
- focus on the nonlinear interaction between sheath and bulk on a nanosecond timescale to understand the differences in voltage and current driven systems

# Particle-In-Cell simulation of an asymmetric ccp



- Id3v PIC simulation with a spherical grid
- system is spherical symmetric  $\implies$  purely 1d along r
- obtain geometrical asymmetry and a self-consistent self-bias

## Voltage and current variation: setup



•  $f_{\rm rf} = 13.56 \, \rm MHz$ 

•  $p_{gas} = 1$  Pa argon

- $L_{gap} = 60 \text{ mm}$
- $V_{\rm rf} = 100.....900 \, \rm V$

- $\frac{A_g}{A_d} = 16$
- $J_{\rm rf} = 10....140 \ {\rm A/m^2}$
- to compare both variations  $\implies S_{abs} = S_e + S_i = \langle \vec{j_c} \cdot \vec{E} \rangle_{x,t}$

# Voltage and current variation: electron density



- voltage source leads to higher densities (same input power!!!)
- especially for higher absorbed power, density difference about 20%
- how is the absorbed power divided?  $\implies$   $S_{abs} = S_e + S_i$

# Voltage and current variation: power distribution



- ion power absorption dominates for higher input power
- 1-2% differences in the electron an ion power absorption
- voltage source puts more power into the electron dynamics
- nonlinear electron resonance heating<sup>1</sup> (NERH) enhances the ionization
- compare 700 V and 100 A/m<sup>2</sup> ( $0.5 \cdot 10^5$  W/m<sup>3</sup>) in more detail

<sup>1</sup>T. Mussenbrock and R.P. Brinkmann, Appl. Phys. Lett. 88, 151503 (2006)

Sebastian Wilczek | GEC Bochum | October 14, 2016

## Current/Voltage at the electrode and the Fourier spectra

### RUB

### voltage source: 700 V









## **Spatio-temporal electron density**

### RUB

### voltage source: 700 V







## Spatio-temporal electron power density

#### voltage source: 700 V









## Spatio-temporal electron power density

#### voltage source: 700 V









### RUB

## Fast electrons above 15.76 eV

### voltage source: 700 V









## Fast electrons above 15.76 eV

#### voltage source: 700 V









### **Ionization rate**

### voltage source: 700 V









### Beam electrons vs. bulk electrons

### voltage source: 700 V









### Beam electrons vs. bulk electrons

### voltage source: 700 V









# Conclusion

- significant differences of current and voltage driven discharges
- different power distribution of the absorbed electron and ion power
- voltage sources represent the correct physics of asymmetric ccrf discharges
- nonlinear electron resonance heating plays a crucial role for the ionization process in voltage driven systems
- electron beam excites the bulk electrons which are attracted back to the sheath<sup>2</sup>
- nonlinear interaction with the plasma sheath leads to multiple electron beams and the generation of harmonics in the current

Outlook:

 even in symmetric discharges significant differences occur, especially at low pressures (~1 Pa)

<sup>&</sup>lt;sup>2</sup>Wilczek et al., Phys. Plasmas. 23, 063514 (2016)